

Process for forming a dual damascene structure

ABSTRACT

5 The invention describes a method for forming a dual
damascene structure. An etch stop layer (150) is formed on
a dielectric layer (140). A second dielectric layer (160)
is formed on the etch stop layer (150) and an ARC layer
(170) is formed the second dielectric layer. A first trench
10 (185) and a second trench (195) are then simultaneously
formed in the first and second dielectric layers (140) and
(160) respectively.